



SEC.506

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of

Byoung-taek Lee et al.

Group Art Unit: 2823

#15/B
Bmt
J. McMillan

Serial No.: 09/276,803

Examiner: N. Berezny

Filed: March 26, 1999

For: METHOD FOR MANUFACTURING CAPACITOR OF SEMICONDUCTOR DEVICE HAVING DIELECTRIC LAYER OF HIGH DIELECTRIC CONSTANT

PRELIMINARY AMENDMENT

Honorable Assistant Commissioner for Patents

Washington, D.C. 20231

Date: July 30, 2002

Sir:

Preliminary to examination of this Continued Prosecution Application (CPA) and responsive to the Office Action dated January 30, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

In the Claims:

The following replacement claim is respectfully submitted:

9. (Twice Amended) A method for manufacturing a capacitor of a semiconductor

device, comprising:

forming a storage electrode over a semiconductor substrate;

forming a high dielectric layer over the storage electrode;

forming a plate electrode over the high dielectric layer;

RECEIVED
AUG 12 2002
TECHNOLOGY CENTER 2800

RECEIVED
AUG 12 2002
TECHNOLOGY CENTER 2800